

U.S. Patent Documents

Examiner	T					Sub-	Filing
Initial	No.	Patent No.	Date	Patentee	Class	class	Date
12.	A	6,204,139	2001-03-20	Liu et al.			
1	В	5,920,500	1999-07-06	Tehrani et al.			
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	Е	6,483,736	2002-11-19	Johnson et al.		T	
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Initial	No.	No.	Date	
<i>b</i> .	J	2002/0000597 A1	01/03/02	Okazawa
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Other Documents

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Bu	L	Beck, A. et al., "Reproducible switching effect in thin oxide films for memory applications", Applied Physics Letters, Vol. 77, No. 1, 3 July 2000,139-141.			
	М	Rossel, C. et al., "Electrical current distribution across a metal-insulator- metal structure during bistable switching", Journal of Applied Physics, Vol. 90, No. 6, 15 September 2001, 2892-2898.			
m	N	Watanabe, Y. et al., "Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped SrTiO ₂ single crystals", Applied Physics Letters, Vol. 78, No. 23, 4 June 2001, 3738-3740.			
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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified)

Information Disclosure
Statement By Applicant

(Use Several Sheets if Necessary)

Atty Docket No. Application No.:
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Applicant:
Rinerson et al.
Filing Date Group
July 1, 2003 2818

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Bu	A	Liu, S.Q., et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films", Applied Physics Letters, Vol. 76, No. 19, 8 May 2000, 2749-2651.
Bu	В	Liu, S.Q., et al., "A New Concept For Non-Volatile Memory: Electric-Pulse Induced Reversible Resistance Change Effect In Magnetoresistive Films", Space Vacuum Epitaxy Center, University of Huston, Huston TX, 7 Pages.
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